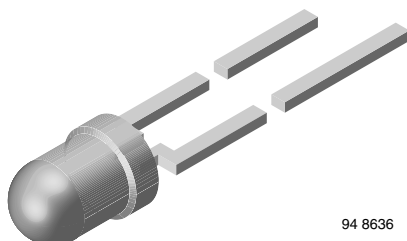


## High Speed Infrared Emitting Diode, RoHS Compliant, 940 nm, GaAIAs, DDH



### FEATURES

- Package type: leaded
- Package form: T-1, clear epoxy
- Dimensions: Ø 3 mm
- Peak wavelength:  $\lambda_p = 940$  nm
- High speed
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching to Si photodetectors
- Lead (Pb)-free component
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### DESCRIPTION

VSLB3940 is a high speed infrared emitting diode in GaAIAs, DDH technology, molded in a clear plastic package.

### APPLICATIONS

- Infrared remote control units

### PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\phi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
VSLB3940	65	$\pm 22$	940	15

#### Note

Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSLB3940	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.1$ , $t_p = 100 \mu\text{s}$	$I_{FM}$	1.0	A
Surge forward current	$t_p = 100 \mu\text{s}$	$I_{FSM}$	1.5	A
Power dissipation		$P_V$	160	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
Operating temperature range		$T_{amb}$	- 25 to + 85	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	300	K/W

#### Note

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

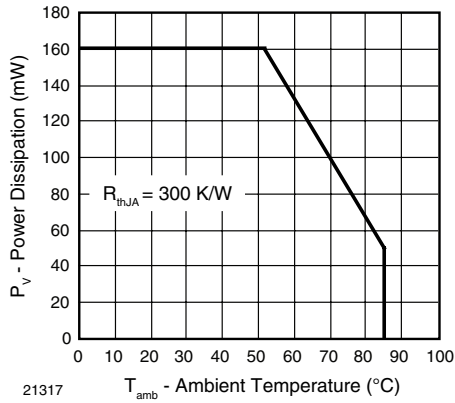


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

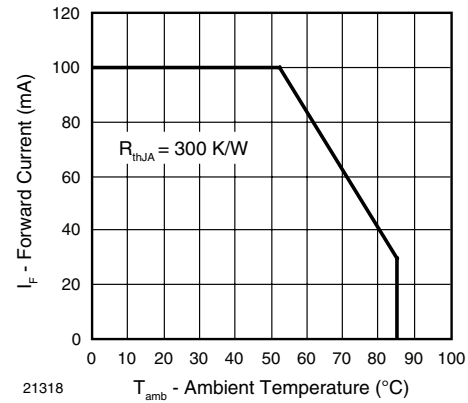


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>	1.15	1.35	1.6	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>		2.2		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>V<sub>F</sub></sub>		- 1.5		mV/K
	I <sub>F</sub> = 100 mA	TK <sub>V<sub>F</sub></sub>		- 1.1		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μA
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0 mW/cm <sup>2</sup>	C <sub>J</sub>		70		pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	I <sub>e</sub>	32	65	110	mW/sr
Radiant power	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	φ <sub>e</sub>		40		mW
Temperature coefficient of radiant power	I <sub>F</sub> = 1 mA	TK <sub>φ<sub>e</sub></sub>		- 1.1		%/K
	I <sub>F</sub> = 100 mA	TK <sub>φ<sub>e</sub></sub>		- 0.51		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I <sub>F</sub> = 30 mA	λ <sub>p</sub>		940		nm
Spectral bandwidth	I <sub>F</sub> = 30 mA	Δλ		25		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 30 mA	TK <sub>λ<sub>p</sub></sub>		0.25		nm
Rise time	I <sub>F</sub> = 100 mA, 20 % to 80 %	t <sub>r</sub>		15		ns
Fall time	I <sub>F</sub> = 100 mA, 20 % to 80 %	t <sub>f</sub>		15		ns
Virtual source diameter		d		2		mm

**Note**

 T<sub>amb</sub> = 25 °C, unless otherwise specified

**BASIC CHARACTERISTICS**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

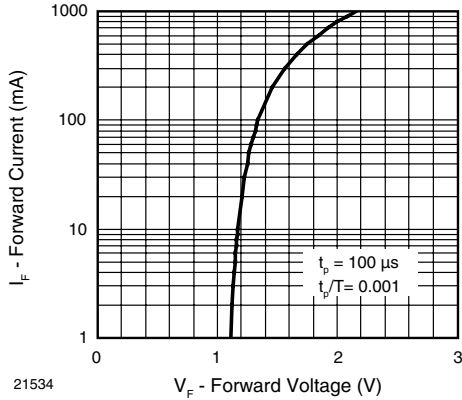


Fig. 3 - Forward Current vs. Forward Voltage

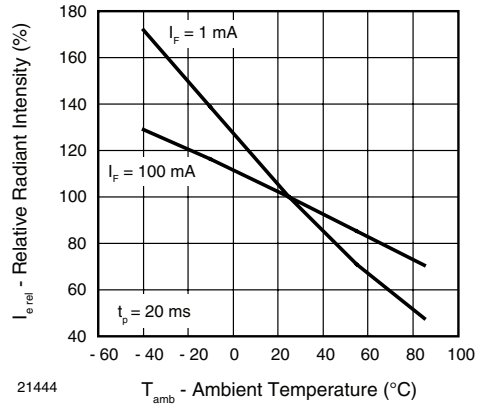


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

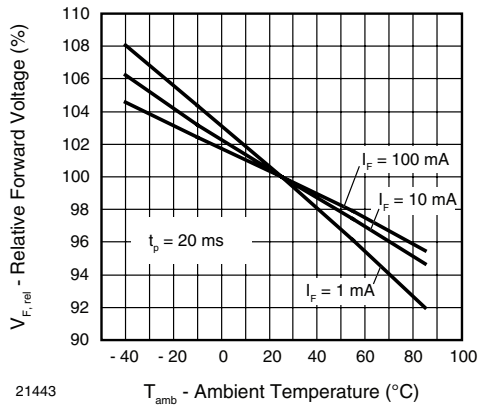


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

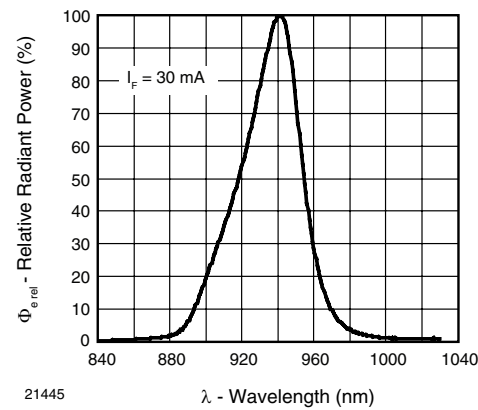


Fig. 7 - Relative Radiant Power vs. Wavelength

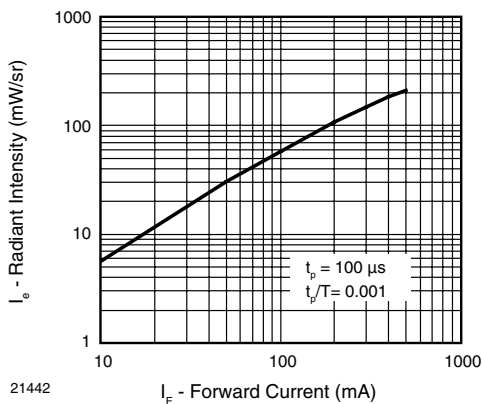


Fig. 5 - Radiant Intensity vs. Forward Current

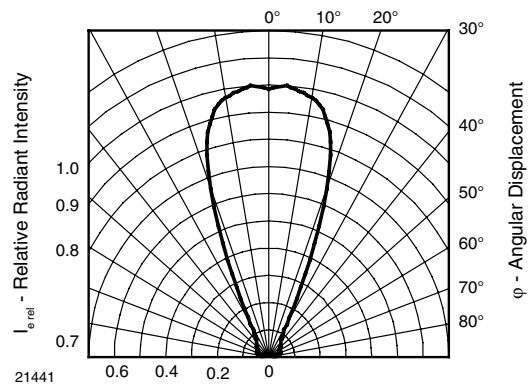
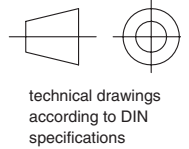
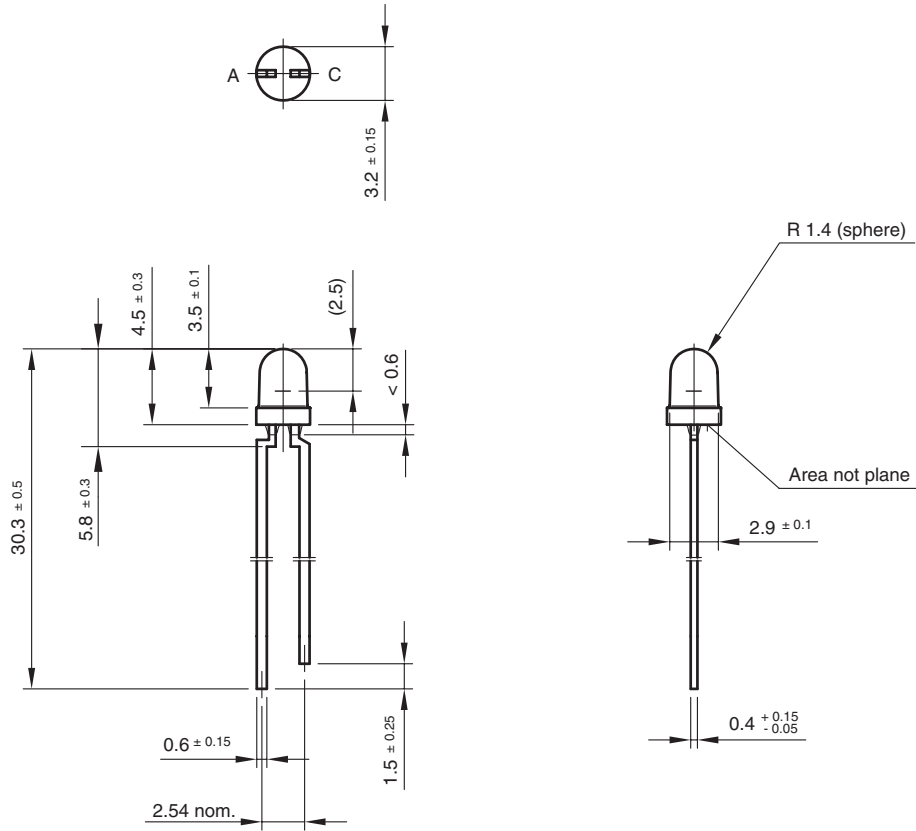


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



**PACKAGE DIMENSIONS** in millimeters



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